

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6166401").PN.	USPAT	OR	OFF	2005/02/14 12:41
L2	1	1 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCl or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous)	USPAT	OR	ON	2005/02/14 12:55
L3	1	"5801401".PN.	USPAT; USOCR	OR	ON	2005/02/14 12:45
L4	1	"5670790".PN.	USPAT; USOCR	OR	ON	2005/02/14 12:45
L5	1	("6166401").PN.	USPAT	OR	OFF	2005/02/14 12:49
L6	1	5 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCl or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous)	USPAT	OR	ON	2005/02/14 12:51
L7	1	3 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCl or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous)	USPAT	OR	ON	2005/02/14 12:51
L8	1	("6586797").PN.	USPAT	OR	OFF	2005/02/14 12:51
L9	1	8 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCl or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous)	USPAT	OR	ON	2005/02/14 12:51

2/14/05

L10	1	1 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCI or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous or oxygen or chlorine or hydrogen)	USPAT	OR	ON	2005/02/14 12:58
L11	1	4 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCI or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous or oxygen or chlorine or hydrogen)	USPAT	OR	ON	2005/02/14 12:59
L12	1	3 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCI or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous or oxygen or chlorine or hydrogen)	USPAT	OR	ON	2005/02/14 12:59
L13	1	8 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCI or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous or oxygen or chlorine or hydrogen)	USPAT	OR	ON	2005/02/14 13:04
L14	1	("6680487").PN.	USPAT	OR	OFF	2005/02/14 13:03
L15	1	14 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCI or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous or oxygen or chlorine or hydrogen)	USPAT	OR	ON	2005/02/14 13:05
L16	1	("6731531").PN.	USPAT	OR	OFF	2005/02/14 13:05

L17	1	16 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCl or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous or oxygen or chlorine or hydrogen)	USPAT	OR	ON	2005/02/14 13:11
L18	1	("6746893").PN.	USPAT	OR	OFF	2005/02/14 13:07
L19	1	18 and (control or gate or floating or nitride or oxide or silicon or polysilicon or insulating or dielectric or HCl or DCl or thickness or microcrystalline or "50" or "200" or "300" or angstroms or reaction or gas or thermal or dope or doping or amorphous or oxygen or chlorine or hydrogen)	USPAT	OR	ON	2005/02/14 13:08
L20	1	("6762068").PN.	USPAT	OR	OFF	2005/02/14 13:08
L21	1	("6794255").PN.	USPAT	OR	OFF	2005/02/14 13:09
L22	1	("6835638").PN.	USPAT	OR	OFF	2005/02/14 13:09
L23	1590	438/197	USPAT	OR	ON	2005/02/14 13:11
L24	2548	438/257	USPAT	OR	ON	2005/02/14 13:12
L25	597	438/263	USPAT	OR	ON	2005/02/14 13:12
L26	1433	438/264	USPAT	OR	ON	2005/02/14 13:12
L27	1236	438/381	USPAT	OR	ON	2005/02/14 13:12
L28	1200	438/680	USPAT	OR	ON	2005/02/14 13:12
L29	606	438/681	USPAT	OR	ON	2005/02/14 13:12
S39	1	("5914896").PN.	USPAT	OR	OFF	2005/02/14 09:57
S40	1	("6381670").PN.	USPAT	OR	OFF	2005/02/14 10:36
S41	38	MOS and control and floating and gate and reaction and gas and microcrystalline and material	USPAT	OR	ON	2005/02/14 10:38
S42	13	MOS and control and floating and gate and reaction and gas and microcrystalline and material and polysilicon and oxide and nitride	USPAT	OR	ON	2005/02/14 12:41